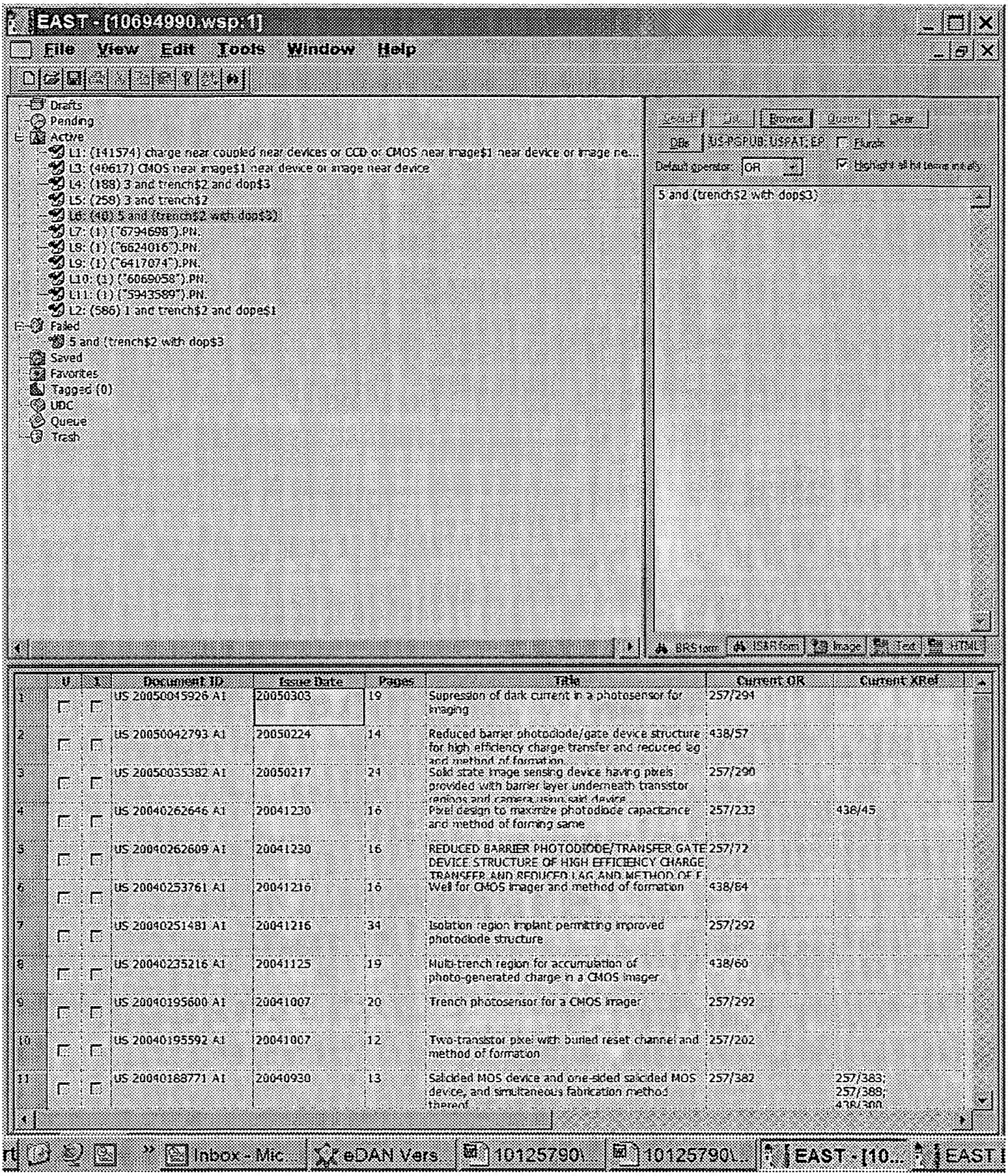

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1			US 20050045926 A1	20050303	19	Supression of dark current in a photosensor for imaging	257/294	
2			US 20050042793 A1	20050224	14	Reduced barrier photodiode/gate device structure for high efficiency charge transfer and reduced lag and method of formation	438/57	
3			US 20050035382 A1	20050217	24	Solid state image sensing device having pixels provided with barrier layer underneath transistor regions and camera using said device	257/290	
4			US 20040262646 A1	20041230	16	Pixel design to maximize photodiode capacitance and method of forming same	257/233	438/45
5			US 20040262609 A1	20041230	16	REDUCED BARRIER PHOTODIODE/TRANSFER GATE DEVICE STRUCTURE OF HIGH EFFICIENCY CHARGE TRANSFER AND REDUCED LAG AND METHOD OF F	257/72	
6			US 20040253761 A1	20041216	16	Well for CMOS imager and method of formation	438/84	
7			US 20040251481 A1	20041216	34	Isolation region implant permitting improved photodiode structure	257/292	
8			US 20040235216 A1	20041125	19	Multi-trench region for accumulation of photo-generated charge in a CMOS imager	438/60	
9			US 20040195600 A1	20041007	20	Trench photosensor for a CMOS imager	257/292	
10			US 20040195592 A1	20041007	12	Two-transistor pixel with buried reset channel and method of formation	257/202	
11			US 20040188771 A1	20040930	13	Salicided MOS device and one-sided salicided MOS device, and simultaneous fabrication method therefor	257/382	257/383; 257/388; 438/300